
HAT1033T

Silicon P Channel Power MOS FET
High Speed Power Switching

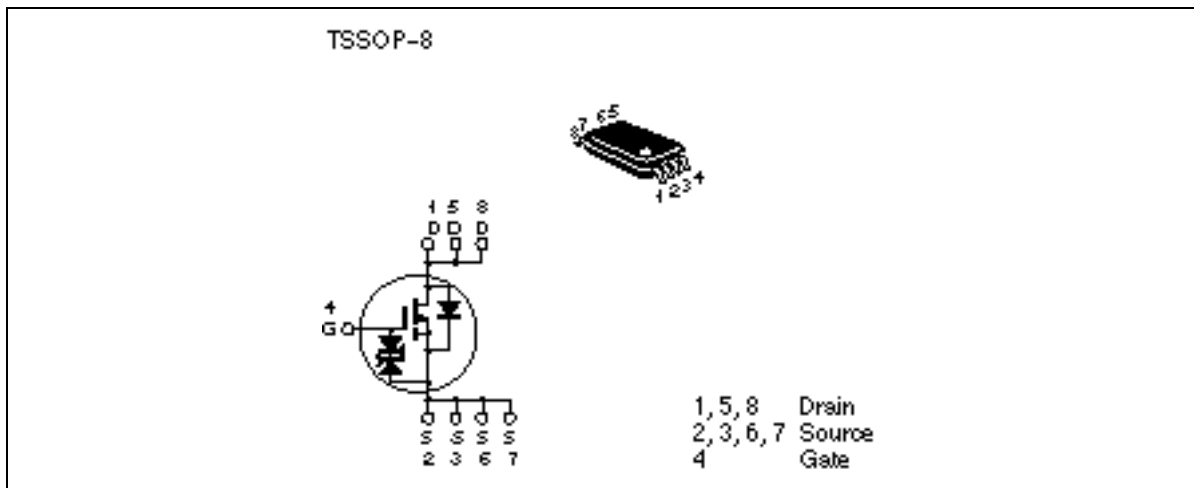
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ADE-208-532 E (Z)
6th. Edition
July 1997

Features

- ¥ Low on-resistance
- ¥ Capable of 2.5 V gate drive
- ¥ Low drive current
- ¥ High density mounting

Outline



HAT1033T

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	-20	V
Gate to source voltage	V _{GSS}	±10	V
Drain current	I _D	-3.5	A
Drain peak current	I _{D(pulse)} * ¹	-28	A
Body to drain diode reverse drain current	I _{DR}	-3.5	A
Channel dissipation	P _{ch} * ²	1.3	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10μs, duty cycle ≤ 1 %

2. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW² 10s

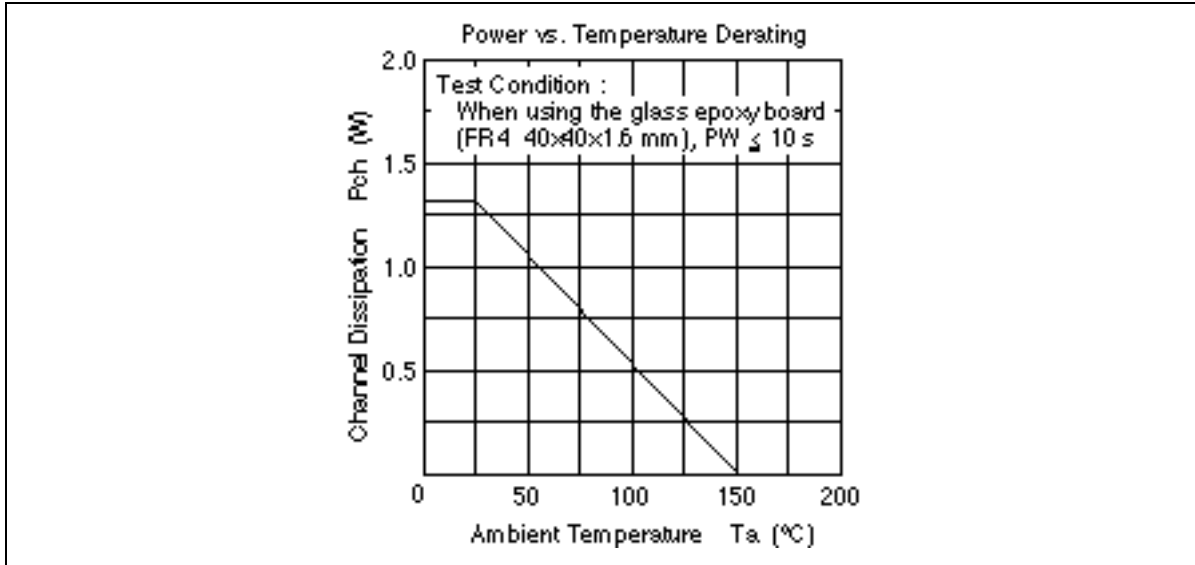
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-20	—	—	V	$I_D = -10\text{mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 10	—	—	V	$I_G = \pm 100\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 8\text{V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -20\text{V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.4	—	-1.4	V	$V_{DS} = -10\text{V}$, $I_D = -1\text{mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.046	0.063	Ω	$I_D = -2\text{A}$, $V_{GS} = -4\text{V}^{*1}$
	$R_{DS(on)}$	—	0.061	0.090	Ω	$I_D = -2\text{A}$, $V_{GS} = -2.5\text{V}^{*1}$
Forward transfer admittance	$ y_{fs} $	5.0	8.0	—	S	$I_D = -2\text{A}$, $V_{DS} = -4\text{V}^{*1}$
Input capacitance	C_{iss}	—	970	—	pF	$V_{DS} = -10\text{V}$
Output capacitance	C_{oss}	—	510	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	150	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	16	—	ns	$V_{GS} = -4\text{V}$, $I_D = -2\text{A}$
Rise time	t_r	—	100	—	ns	$V_{DD} \cong -10\text{V}$
Turn-off delay time	$t_{d(off)}$	—	245	—	ns	
Fall time	t_f	—	190	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-0.81	-1.06	V	$I_F = -3.5\text{A}$, $V_{GS} = 0^{*1}$
Body to drain diode reverse recovery time	t_{rr}	—	65	—	ns	$I_F = -3.5\text{A}$, $V_{GS} = 0$ $di_F/dt = 20\text{A}/\mu\text{s}$

Note: 1. Pulse test

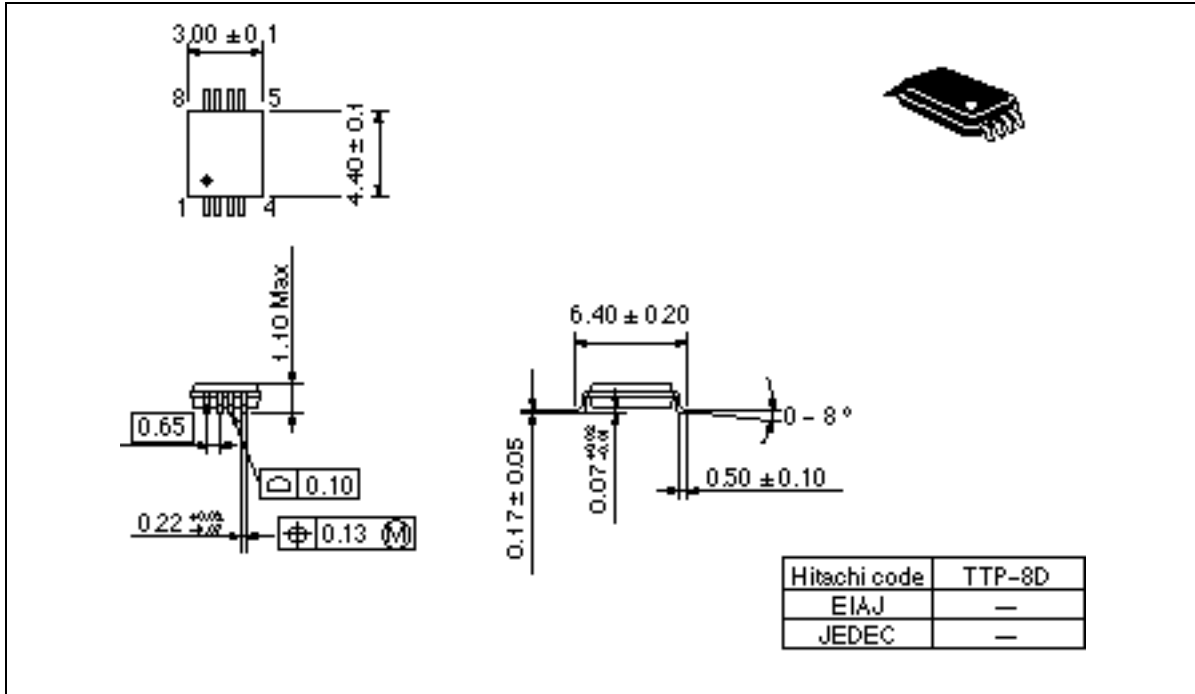
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Main Characteristics



Package Dimensions

Unit: mm



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